Transistor Using Two-dimensional Electron Gas in Thin Film Oxide Heterostructure via Atomic Layer Deposition

Hye Ju Kim, Seong Hwan Kim, and Sang Woon Lee
Department of Energy Systems Research and Department of Physics, Ajou University
Suwon 16499, Republic of Korea
ajuphysics@ajou.ac.kr; paullikebe77@gmail.com; slee01@ajou.ac.kr

Extended Abstract

Two-dimensional electron gas (2DEG) at an epitaxial interface of LaAlO₃/SrTiO₃ (LAO/STO) heterostructures has received considerable attentions because of their unique physical properties.[1] Electrons at the interface of LAO/STO heterostructure move freely along in-plane direction while they are confined in 1~2 nm range of out-of-plane direction. The electron density of 2DEG at LAO/STO heterostructure is $10^{13}$~$10^{14}/$cm² which is 100 times higher than those of the conventional semiconductor heterojunction such as AlGaAs/GaAs. The high density of electrons enables a fabrication of high-performance transistor. Unfortunately, the growth of LAO epitaxial layer on single crystalline STO substrate is necessary for 2DEG generation via polar catastrophe mechanism which impeded a practical use of the oxide heterostructure.

Here, we demonstrated a creation of 2DEG at the non-epitaxial interface of Al₂O₃/TiO₂ (<15 nm) thin film heterostructure via atomic layer deposition (ALD), without using single crystalline STO substrate for the first time.[2] By implementing ALD, the mature thin film process can facilitate mass production as well as three-dimensional integration of the devices. The electrical properties of thin film Al₂O₃/TiO₂ heterostructure are similar with those of the epitaxial LAO/STO heterostructures. It was observed that high density electrons up to ($10^{13}$~$10^{14}$/cm²) were confined within ~2.2 nm of the interface of the Al₂O₃/TiO₂ heterostructure. Interestingly, the electron density can be adjusted from ~ $10^{11}$/cm² to ~ $10^{14}$/cm² by the control of ALD process temperature because the free electrons are created by the formation of oxygen vacancies at the interface of Al₂O₃/TiO₂ heterostructure of which kinetics is governed by the ALD process temperature. Those oxides (Al₂O₃ and TiO₂) are transparent insulators with wide bandgaps (>3.2 eV) which implies a possible application of transparent devices.

With the Al₂O₃/TiO₂ thin film heterostructure, a transparent thin film transistor (TFT) was fabricated which outperforms conventional TFTs. A high on-current ($I_{on}$ > 12 μA/μm), high on/off current ratio ($I_{on}/I_{off}$ > $10^8$), low off-current ($I_{off}$, ~$10^{-8}$ μA/μm), and low sub-threshold swing (SS, ~100 mV/dec.) are achieved. Besides the TFT application, a high-performance transparent hydrogen (H₂) gas sensor was developed using the 2DEG at Al₂O₃/TiO₂ thin film heterostructure which shows a sensitive detection of H₂ gas even at room temperature.[3] It exhibited a reliable detection with a fast response speed (<30 s) for H₂ concentration as low as 5 ppm which outperforms conventional H₂ gas sensors operating at room temperature, indicating that heating modules are not required for the rapid detection of H₂. The gas sensor can detect H₂ gas across a wide range of concentrations, from 5 ppm to 1%, implying that it is a promising candidate for a general H₂ sensor. The H₂ gas sensor using 2DEG was fabricated on a polyimide substrate which enabled a fabrication of flexible gas sensor. The H₂ sensing performance was maintained even after bending cycles of 500 with a bending radius of 10 mm.

After all, the creation and control of 2DEG at thin film oxide heterostructure using ALD, and their applications will be addressed in the presentation.

References
